

Shantou Huashan Electronic Devices Co.,Ltd.

NPN SILICON TRANSISTOR

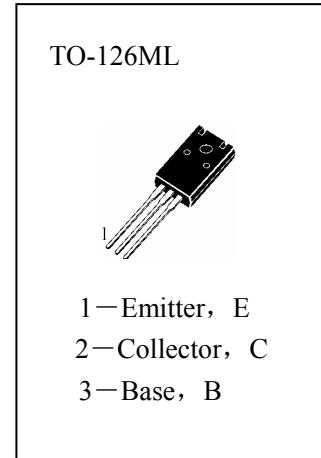
HB123D

■ APPLICATIONS

Power Amplifie

■ ABSOLUTE MAXIMUM RATINGS ($T_a=25^\circ\text{C}$)

T_{stg}	— Storage Temperature	-55~150°C
T_j	— Junction Temperature	150°C
P_C	— Collector Dissipation ($T_C=25^\circ\text{C}$)	10W
V_{CBO}	— Collector-Base Voltage	500V
V_{CEO}	— Collector-Emitter Voltage	400V
V_{EBO}	— Emitter-Base Voltage	8V
I_C	— Collector Current	1A



■ ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$)

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
BVCBO	Collector-Base Breakdown Voltage	500			V	$I_C=1\text{mA}, I_E=0$
BVCEO	Collector-Emitter Breakdown Voltage	400			V	$I_C=10\text{mA}, I_B=0$
BVEBO	Emitter-Base Breakdown Voltage	8			V	$I_E=1\text{mA}, I_C=0$
ICBO	Collector Cut-off Current			10	μA	$V_{CB}=500\text{V}, I_E=0$
HFE (1)	DC Current Gain	10		65		$V_{CE}=5\text{V}, I_C=300\text{mA}$
HFE (2)	DC Current Gain	10				$V_{CE}=5\text{V}, I_C=500\text{mA}$
VCE(sat)	Collector- Emitter Saturation Voltage			0. 3	V	$I_C=100\text{mA}, I_B=10\text{mA}$